NSN 5962-01-391-1181

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View Online at https://aerobasegroup.com/nsn/5962-01-391-1181
Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.320 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
2.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+125.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Monolithic and bipolar and programmable
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Criticality Code Justification:
Feat
Case Outline Source And Designator:
D-8 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
12.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal
Special Features:
Esd, software file no: 8912782-1-701, using module i/o-8905870-511 and location u4
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification

format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

20 printed circuit

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N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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